

Amendments to the Claims

Claims 1-39 (Canceled).

40. (Currently amended) A wafer bonding method of forming silicon-on-insulator-comprising integrated circuitry, comprising:

forming silicon dioxide on at least a portion of an outer surface of a handle wafer;

nitridizing at least a portion of an outer surface of the silicon dioxide effective to form silicon nitride on silicon dioxide;

after the nitridizing, joining the handle wafer with an outer surface of silicon comprised by a device wafer;

forming a pair of source/drain regions separated by a channel region within the silicon, the silicon nitride being received intermediate the source/drain regions and the silicon dioxide and extending only partially across the channel region; and

forming a field effect transistor gate operably proximate the channel region.

41. (Original) The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises crystalline silicon.

42. (Withdrawn) The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises silicon nitride.

43. (Withdrawn) The method of claim 40 wherein the outer surface of the device wafer to which the handle wafer is joined comprises silicon dioxide.

44. (Original) The method of claim 40 wherein the nitridizing comprises ion implanting.

45. (Withdrawn) The method of claim 40 wherein the nitridizing comprises direct plasma nitridation.

46. (Withdrawn) The method of claim 40 wherein the nitridizing comprises remote plasma nitridation.

47. (Withdrawn) The method of claim 40 wherein the nitridizing comprises chemical vapor deposition.

48. (Previously presented) The method of claim 40 wherein the nitridation is void of either direct or remote nitride-containing plasma exposure.

Claims 49-61 (Cancelled).

62. (Previously presented) The method of claim 40 wherein the nitridizing comprises N₂.

63. (Withdrawn) The method of claim 40 wherein the nitridizing comprises NO_x .

64. (Withdrawn) The method of claim 40 wherein the nitridizing comprises NH_3 .

65. (Withdrawn) The method of claim 40 wherein the nitridizing comprises N_2O .

66. (Previously presented) The method of claim 40 wherein the silicon nitride is from about 5 Angstroms to about 50 Angstroms thick.